

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Withdrawn) A semiconductor integrated circuit device including a gate electrode structure comprising at least:

a first conductive region and a second conductive region formed on a semiconductor substrate and separated by an isolation region;

a gate insulator formed on said first conductive region and second conductive region across said isolation region;

a second conductive silicon layer, which is deposited on said first conductive region, and a first conductive silicon layer, which is deposited on said second conductive region, and formed on said gate insulator having a boundary on said isolation region;

a first nitride film of refractory metal, which is formed on said first conductive and second conductive silicon layers and separated at a boundary of said first conductive and second conductive silicon layers; and

a first refractory metal film, which is formed on said first nitride film of refractory metal and separated at a boundary of said first conductive and second conductive silicon layers.

2. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein said first conductive and second conductive silicon layers are also separated.

3. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein a second refractory metal or a second nitride film of refractory metal is embedded in said regions separating first nitride film of refractory metal and first refractory metal.

4. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein:

an insulator is embedded in said regions separating first nitride film of refractory metal and first refractory metal, and

a layer which comprises one type of film selected from titanium nitride, zirconium nitride, and hafnium nitride or a composite film therefrom is formed on said embedded insulator and said first refractory metal.

5. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein a first silicide film of refractory metal is formed between said first nitride film of refractory metal and both of said first conductive and second conductive silicon layers.

6. (Currently Amended) A semiconductor integrated circuit device comprising:

a first conductive type region and a second conductive type region formed in semiconductor substrate and separated by an isolation region;

a gate insulator formed on said first conductive type region and said second conductive type region;

a second conductive type silicon layer which is deposited over said first conductive type region and on said gate insulator, and a first conductive type silicon layer which is deposited over said second conductive type region and on said gate insulator, wherein a boundary between said first conductive type silicon layer and said second ~~conductive~~ conductive type silicon layer is located over said isolation region;

a first nitride film of refractory metal formed on said first conductive type silicon layer, and a second nitride film of refractory metal formed on said second conductive type silicon layer;

a first refractory metal film formed on said first nitride film of refractory metal, and a second refractory metal film formed on said second nitride film of refractory metal; and

a metal carbide formed between said first nitride film of refractory metal and said second nitride ~~file~~ film of refractory metal, between said first refractory metal film and said second refractory metal film, and on said boundary between said first conductive type silicon layer and said second conductive type silicon layer.

7. (Previously Presented) A semiconductor integrated circuit device according to claim 6, wherein, instead of said metal carbide, a metal nitride with high nitrogen concentration or a metal oxide is formed between said first nitride film of refractory

metal and said second nitride film of refractory metal between said first refractory metal film and said second refractory metal film, and said boundary between said first conductive type silicon layer and said second conductive type silicon layer.

8. (Currently Amended) A semiconductor integrated circuit device according to claim 6, wherein a first silicide film of refractory metal is formed between said first and second nitride film films of refractory ~~material~~ metal and said first conductive and second conductive silicon layers.
9. (Withdrawn) A semiconductor integrated circuit device according to claim 1, wherein a non-doped silicon layer or germanium-doped silicon layer is formed between said nitride film of refractory material and said first conductive and second conductive silicon layers.
10. (Previously Presented) A semiconductor integrated circuit device according to claim 6, wherein a first silicide film of refractory metal is formed between said first nitride film of refractory metal and said first conductive type silicon layer, a second silicide film of refractory metal is formed between said second nitride film of refractory metal and said second conductive type silicon layer, and a non-doped silicon layer or a germanium-doped silicon layer is formed between said first silicide film of refractory metal and said first conductive type silicon layer and between said second silicide film of refractory metal and said second conductive type silicon layer.
- 11-20. (Canceled)
21. (Withdrawn) A semiconductor integrated circuit device according to claim 2, wherein a second refractory metal or a second nitride film of refractory metal is embedded in said isolated region of the first nitride film of refractory metal and the first refractory metal.
22. (Withdrawn) A semiconductor integrated circuit device according to claim 2, wherein:

an insulator is embedded in said isolated region of said first nitride film of refractory metal and first refractory film, and

a layer which comprises one type of film selected from titanium nitride, zirconium nitride, and hafnium nitride or a composite film therefrom is formed on said embedded insulator and said first refractory metal.

23. (Withdrawn) A semiconductor integrated circuit device according to claim 2, wherein a first silicide film of refractory metal is formed between said nitride film of refractory metal and said first and second conductive silicon layers.
24. (Previously Presented) A semiconductor integrated circuit device according to claim 7, wherein a first silicide film of refractory metal is formed between said nitride film of refractory metal and said first and second conductive silicon layers.
25. (Previously Presented) A semiconductor integrated circuit device according to claim 6, wherein a non-doped silicon layer or a germanium-doped silicon layer is formed between said first nitride film of refractory metal and said first conductive type silicon layer and between said second nitride film of refractory metal and said second conductive type silicon layer.

26-32. (Canceled)